



W55FXX

SERIAL FLASH EEPROM SERIES

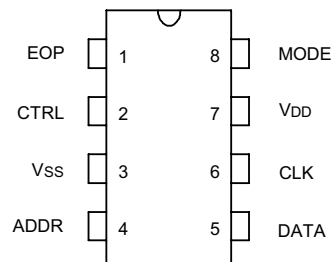
GENERAL DESCRIPTION

The W55FXX is a serial input/output flash EEPROM series that is typically used as the memory cell of a W51300 (voice recorder controller) or the ROM code emulator for the PowerSpeech™ series. The single voltage supply eliminates the need for an extra pump circuit during programming and erasing.

FEATURES

- Provides CLK, ADDR, and DATA pins to operate with Winbond PowerSpeech™ series
- 512K/1M/2M memory sizes available
- Directly cascadable for longer duration
- Fast frame-write operation
 - Frame (32 bits) program cycle time: 400 μ S (typ.)
- Fast whole-chip-erase duration: 50 mS (max.)
- Read data access time: 500 nS (max.)
- Program/erase cycles: 10,000 (typ.)
- Data retention: 10 years (typ.)
- Low power consumption:
 - Operating: 5 mA (typ.)
 - Standby: 2 μ A (typ.)

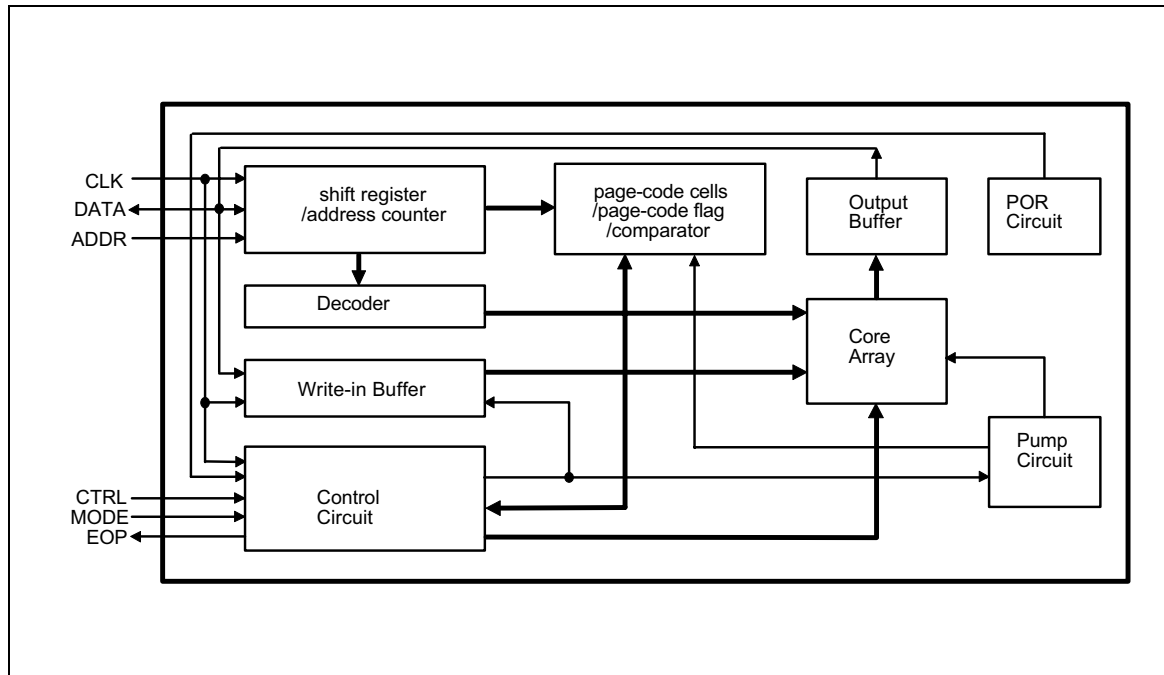
PIN CONFIGURATION



PIN DESCRIPTION

NO.	PIN NAME	I/O	DESCRIPTION
1	EOP	O	End of process signal output
2	CTRL	I	Enable signal for program and erase operations when MODE = 0 Input clock for mode counter when MODE = 1
3	Vss	I	Ground
4	ADDR	I	Input clock for start address shift-in
5	DATA	I/O	Bidirectional data line
6	CLK	I	Input clock for data write-in and read-out
7	VDD	I	Positive voltage supply
8	MODE	I	Mode select control pin

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	CONDITION	RATED VALUE	UNIT
Operating Temp.	TOPR	-	0 to +70	°C
Storage Temp.	TSTG	-	-65 to +150	°C
Power Supply	VDD-VSS	-	-0.3 to +7.0	V
Input DC Voltage	VDC	All pins	-0.5 to VDD +1.0	V
Transient Voltage (< 20 nS)	VTRAN	All pins	-1.0 to VDD +1.0	V

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

DC CHARACTERISTICS

(VDD = 4.5V, VSS = 0V, TA = 25° C)

PARAMETER		SYMBOL	CONDITIONS	LIMITS			UNIT
				MIN.	TYP.	MAX.	
Operating voltage		VDD	-	2.4 (Note)	4.5	5.5	V
Standby current		ISB	All inputs = GND DATA & EOP open	-	2	4	μA
Operating current		IOP	In read mode DATA & EOP open FOSC = 1 MHz	-	5	10	mA
Input voltage	High	VIH	All input pins	2.0		VDD	V
	Low	VIL		-0.3	-	0.8	V
Output current	Sink	IOL	VOL = 0.5V	2.5	5	-	mA
	Drive	IOH	VOH = 4.0V	-2.5	-5	-	mA
Input leakage current of CTRL, MODE		ILI1	VIN = 4.5V	-	-	4.5	μA
Input leakage current of DATA		ILI2	VIN = 0V	-	-	-4.5	μA

Note: For been working with W52900, the minimum operating voltage couldn't be less than 3.6 volt.



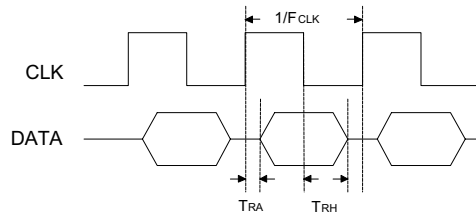
AC CHARACTERISTICS

(VDD = 4.5V, VSS = 0V, TA = 25° C)

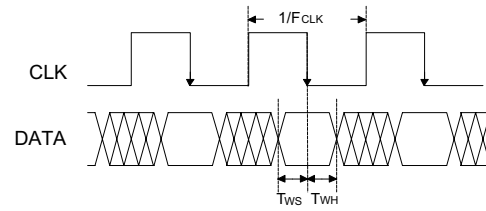
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
MODE pulse width	TMP	-	1	-	-	μS
CTRL pulse width	TWP	Page coding mode	400	-	700	μS
Clock frequency of ADDR	FADDR	-	-	-	1	MHz
Clock frequency of CLK	FCLK	-	-	-	1	MHz
Clock frequency of CTRL	FCTRL	-	-	-	1	MHz
Interval between ADDR end & CLK begin	TI	Read/Write mode	1	-	-	μS
Interval between CLK & CTRL	TGCC	Write mode	1	-	-	μS
Interval between ADDR & CTRL	TGCA	Page coding mode	1	-	-	μS
Interval between addressing end & block-erase begin	TAE	Block erase mode	1	-	-	μS
Interval between MODE rising edge & CTRL clock begin	TMB	Mode selection	500	-	-	nS
Interval between CTRL clock end & MODE falling edge	TME	Mode selection	500	-	-	nS
Interval between MODE falling edge & another pin active	TGM	-	1	-	-	μS
Data access time	TRA	Read mode	-	-	500	nS
Data set up time	TWS	Write mode	250	-	-	nS
	TAS	-	250	-	-	nS
Data hold time	TRH	Read mode	0	-	-	nS
	TWH	Write mode	10	-	-	nS
	TAH	-	10	-	-	nS
Programming duration	TPR	Write mode	400	-	-	μS
Whole-chip-erase time	TWE	Whole-chip-erase mode	45	-	50	mS
Block-erase time	TBE	Block-erase mode	40	-	45	mS

TIMING WAVEFORM

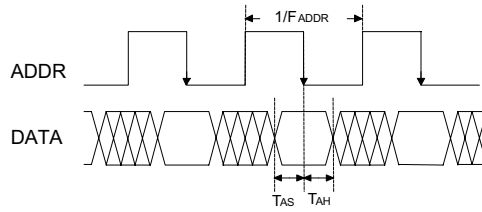
Read Cycle



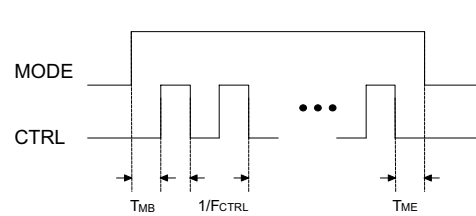
Write Cycle



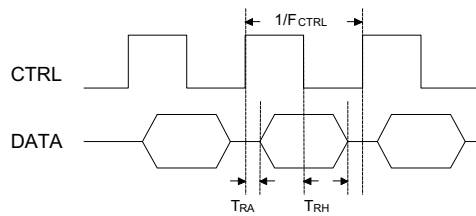
Address Shift-in Cycle



Mode Select Duration



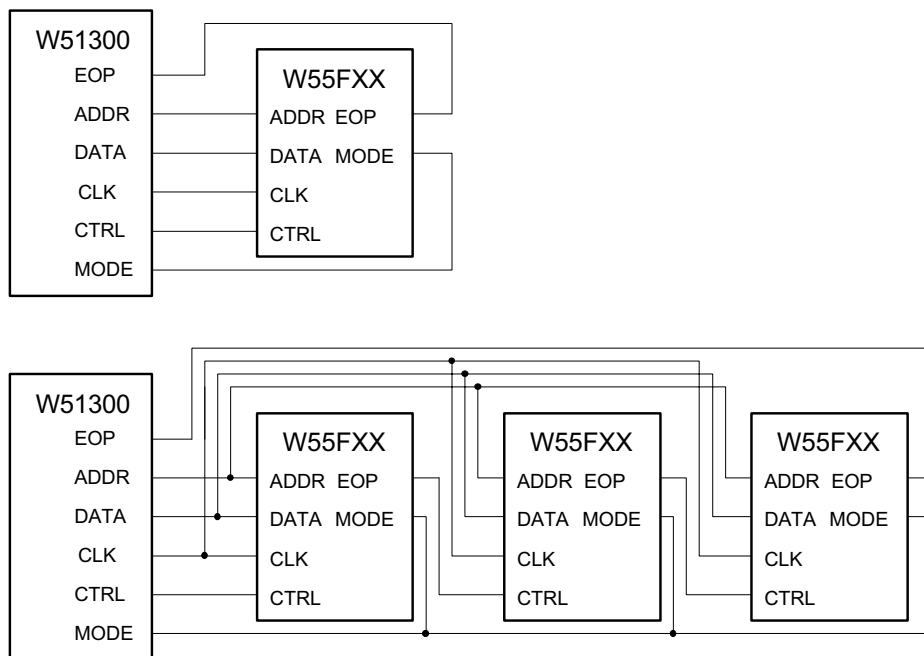
Page-code Cell Read Out Cycle



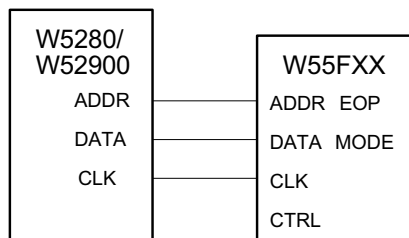
Note: The duty cycle of any clock is 50%.

APPLICATION CIRCUITS (for reference only)

- For Voice Recorder Applications



- For PowerSpeech Applications



ORDERING INFORMATION

PART NO.	MEMORY SIZE
W55F05	512K BITS
W55F10	1M BITS
W55F20	2M BITS



W55FXX



Headquarters

No. 4, Creation Rd. III,
Science-Based Industrial Park,
Hsinchu, Taiwan
TEL: 886-3-5770066
FAX: 886-3-5792697

<http://www.winbond.com.tw/>

Voice & Fax-on-demand: 886-2-7197006

Taipei Office

11F, No. 115, Sec. 3, Min-Sheng East Rd.,
Taipei, Taiwan
TEL: 886-2-7190505
FAX: 886-2-7197502

Winbond Electronics (H.K.) Ltd.

Rm. 803, World Trade Square, Tower II,
123 Hoi Bun Rd., Kwun Tong,
Kowloon, Hong Kong
TEL: 852-27516023
FAX: 852-27552064

Winbond Electronics North America Corp.

Winbond Memory Lab.
Winbond Microelectronics Corp.
Winbond Systems Lab.

2730 Orchard Parkway, San Jose,
CA 95134, U.S.A.
TEL: 1-408-9436666
FAX: 1-408-9436668

Note: All data and specifications are subject to change without notice.